

## CLAIMS

1. A high frequency circuit characterized by comprising:

5 a plurality of shunt paths including active elements and  
impedance elements in between a high frequency transmission  
path and a ground;

wherein said plurality of shunt circuits form a parallel  
resonance circuit of said impedance elements when each of said  
active elements is ON, and a serial resonance circuit of said  
10 impedance elements when each of said active elements is OFF.

2. The high frequency circuit according to claim 1  
characterized in that:

15 said active element is a field effect transistor.

3. The high frequency circuit according to claim 2  
characterized in that:

20 said field effect transistor is made of gallium arsenic  
series material.

4. The high frequency circuit according to claim 1  
characterized in that:

25 said plurality of shunt paths are formed on a same  
substrate.

5. The high frequency circuit according to claim 1  
characterized in that:

an inductor forming said plurality of shunt paths is  
replaced with inductance components of an IC bonding wire.